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	INFORMATIO	N DISCLOSURE		Filing Date	Herewith	
STATEMENT BY APPLICANT				First Named Inventor	Srinivasan Chakravarthi, et al.	
(use as many sheets as necessary)				Group Art Unit	2813	
				Examiner Name	Yennhu B. Huyh	
Sheet	1	of	1	Attorney Docket No.	TI-33161.1	

				U.S. 1	PATENT DOCUME	ENTS
	Cite No.1	U.S. Patent Document		Name of Patentee	Date of Pub.	
Exam. Initials*		Number	Kind Code <sup>2</sup> (if known)	or Applicant of Cited Doc.	of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figure Appear
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	FOREIGN PATENT DOCUMENTS								
		Foreign Patent Document			Name of Patentee	Date of Pub.			
Exam. Initials*	Cite No. <sup>1</sup>	Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>2</sup> (if known)	or Applicant of Cited Doc.	of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>	
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		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Exam. Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
-	CA	P. PACKAN ET AL., "Modeling Solid Source Boron Diffusion for Advanced Transistor Applications" IEEE, IEDM 98, pp. 505-508	
	СВ	DANIEL F. DOWNEY ET AL., "Effect of Fluorine on the Diffusion of Boron in Ion Implanted Si* 1998 American Institute of Physics, Vol. 73, Number 9, August 31, 1998, pp. 1263-1265	
	СС		
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Examiner	Date
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